

General Description

This planar stripe MOSFET has better characteristics, such as fast switching time, low on resistance, low gate charge and excellent avalanche characteristics. It is mainly suitable for electronic ballast and switching mode power supplies.

FEATURES

- $V_{DSS} = 500V$, $I_D = 5.0A$
- Drain-Source ON Resistance : $R_{DS(ON)} = 1.4$ @ $V_{GS} = 10V$
- $Q_g(\text{typ}) = 12nC$

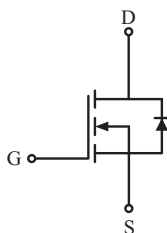
MAXIMUM RATING (Tc=25)

CHARACTERISTIC	SYMBOL	RATING		UNIT	
		KF5N50P KF5N50PZ	KF5N50F KF5N50FZ		
Drain-Source Voltage	V_{DSS}	500		V	
Gate-Source Voltage	V_{GSS}	± 30		V	
Drain Current	@Tc=25	I_D	5.0	5.0*	
	@Tc=100		2.9	2.9*	
	Pulsed (Note1)		I_{DP}	13	13*
Single Pulsed Avalanche Energy (Note 2)	E_{AS}	270		mJ	
Repetitive Avalanche Energy (Note 1)	E_{AR}	8.6		mJ	
Peak Diode Recovery dv/dt (Note 3)	dv/dt	4.5		V/ns	
Drain Power Dissipation	Tc=25	P_D	83	41.5	W
	Derate above 25		0.66	0.33	W/
Maximum Junction Temperature	T_j	150			
Storage Temperature Range	T_{stg}	-55 150			
Thermal Characteristics					
Thermal Resistance, Junction-to-Case	R_{thJC}	1.5	3.0	/W	
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62.5	62.5	/W	

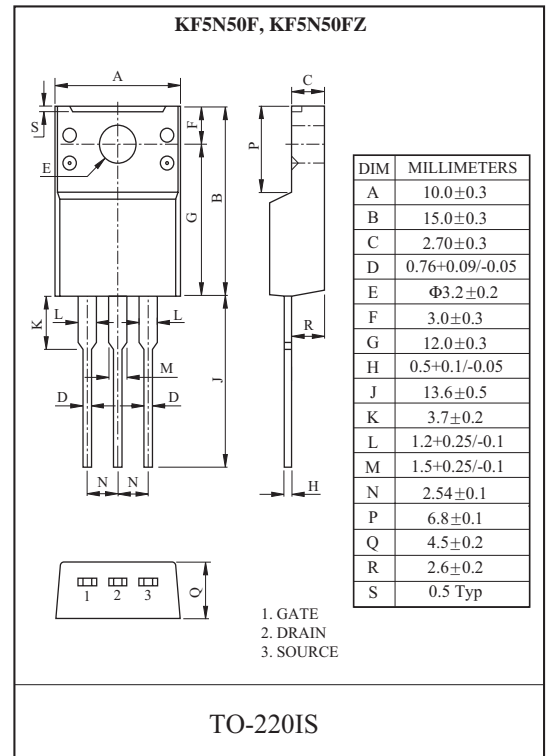
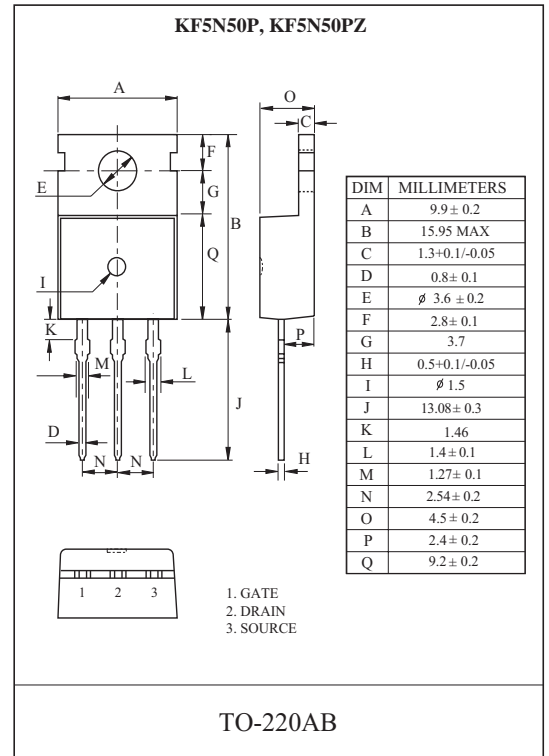
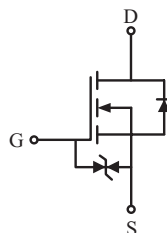
* : Drain current limited by maximum junction temperature.

PIN CONNECTION

(KF5N50P, KF5N50F)



(KF5N50PZ, KF5N50FZ)



KF5N50P/F/PZ/FZ

ELECTRICAL CHARACTERISTICS (Tc=25)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	500	-	-	V
Breakdown Voltage Temperature Coefficient	BV _{DSS} / T _j	I _D =250μA, Referenced to 25	-	0.55	-	V/
Drain Cut-off Current	I _{DSS}	V _{DS} =500V, V _{GS} =0V,	-	-	10	μA
Gate Threshold Voltage	V _{th}	V _{DS} =V _{GS} , I _D =250μA	2.0	-	4.0	V
Gate Leakage Current	I _{GSS}	KF5N50P/F V _{GS} = ± 30V, V _{DS} =0V	-	-	± 100	nA
		KF5N50PZ/FZ V _{GS} = ± 25V, V _{DS} =0V	-	-	± 10	μA
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =2.5A	-	1.15	1.4	
Dynamic						
Total Gate Charge	Q _g	V _{DS} =400V, I _D =5A V _{GS} =10V (Note4,5)	-	12	-	nC
Gate-Source Charge	Q _{gs}		-	2.4	-	
Gate-Drain Charge	Q _{gd}		-	5.4	-	
Turn-on Delay time	t _{d(on)}	V _{DD} =250V R _L =50 R _G =25 (Note4,5)	-	22.5	-	ns
Turn-on Rise time	t _r		-	29	-	
Turn-off Delay time	t _{d(off)}		-	58	-	
Turn-off Fall time	t _f		-	18	-	
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	430	-	pF
Output Capacitance	C _{oss}		-	71	-	
Reverse Transfer Capacitance	C _{rss}		-	7.5	-	
Source-Drain Diode Ratings						
Continuous Source Current	I _S	V _{GS} <V _{th}	-	-	5	A
Pulsed Source Current	I _{SP}		-	-	20	
Diode Forward Voltage	V _{SD}	I _S =5A, V _{GS} =0V	-	-	1.4	V
Reverse Recovery Time	t _{rr}	I _S =5A, V _{GS} =0V, dI _S /dt=100A/μs	-	150	-	ns
Reverse Recovery Charge	Q _{rr}		-	0.42	-	μC

Note 1) Repetivity rating : Pulse width limited by junction temperature.

Note 2) L=19.5mH, I_S=5A, V_{DD}=50V, R_G=25 , Starting T_j=25 .

Note 3) I_S 5A, dI/dt 100A/μs, V_{DD} BV_{DSS}, Starting T_j=25 .

Note 4) Pulse Test : Pulse width 300μs, Duty Cycle 2%.

Note 5) Essentially independent of operating temperature.

Marking

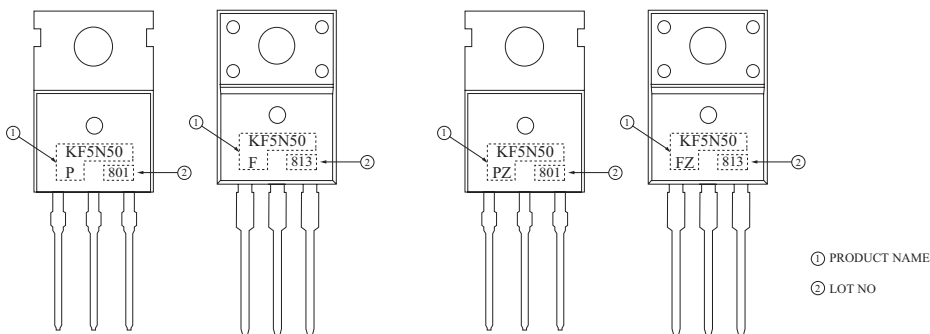


Fig1. $I_D - V_{DS}$

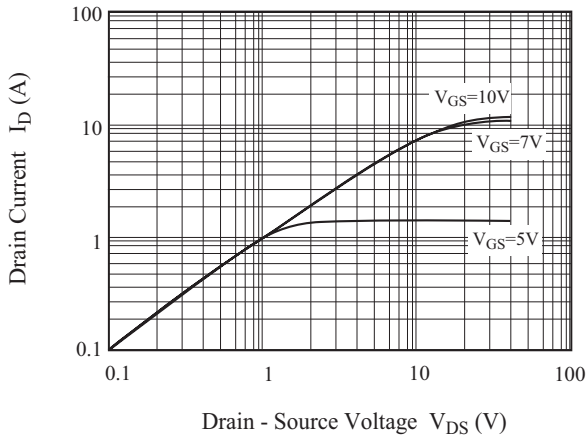


Fig2. $I_D - V_{GS}$

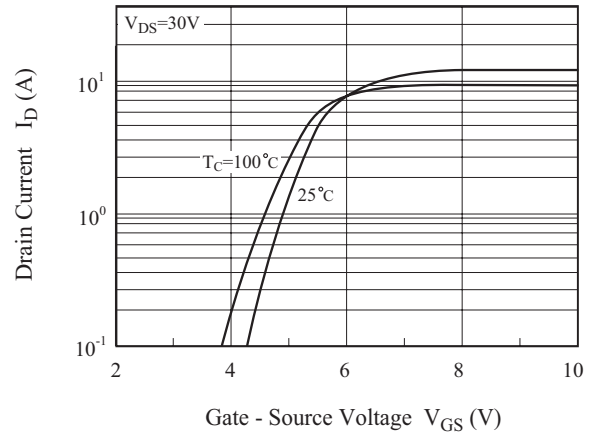


Fig3. $BV_{DSS} - T_j$

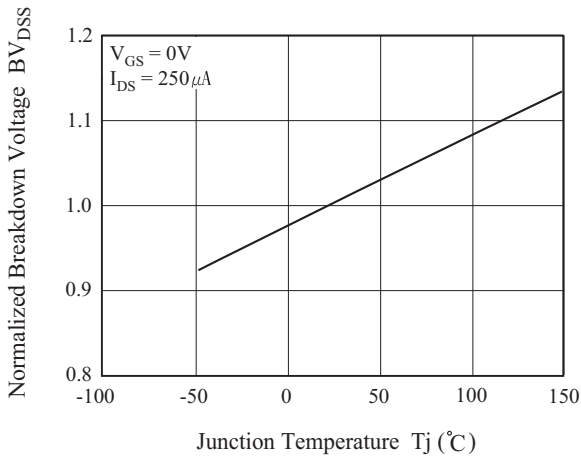


Fig4. $R_{DS(ON)} - I_D$

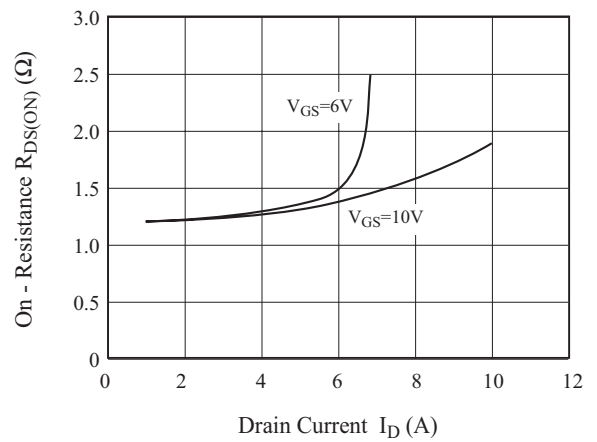


Fig5. $I_S - V_{SD}$

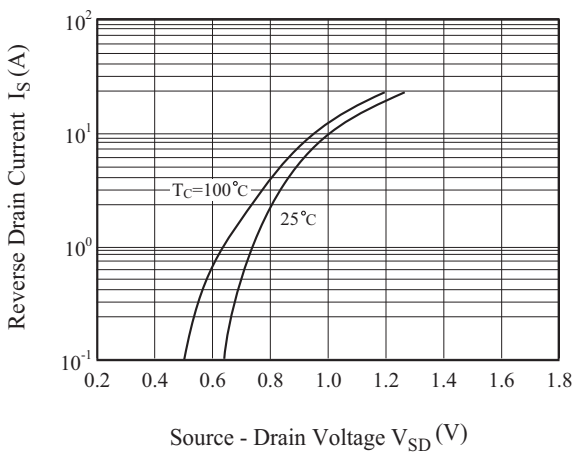
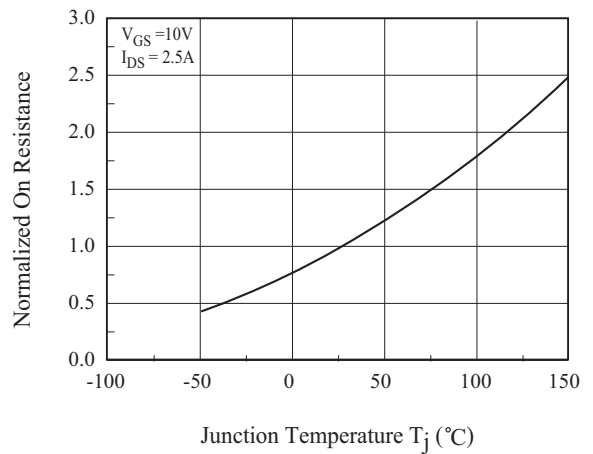


Fig6. $R_{DS(ON)} - T_j$



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Fig 7. C - V_{DS}

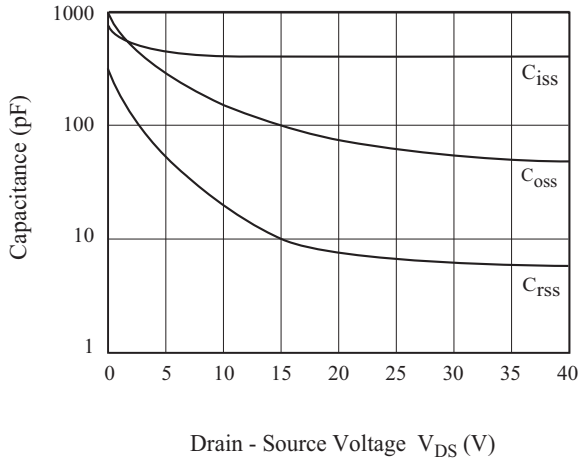


Fig8. Q_g - V_{GS}

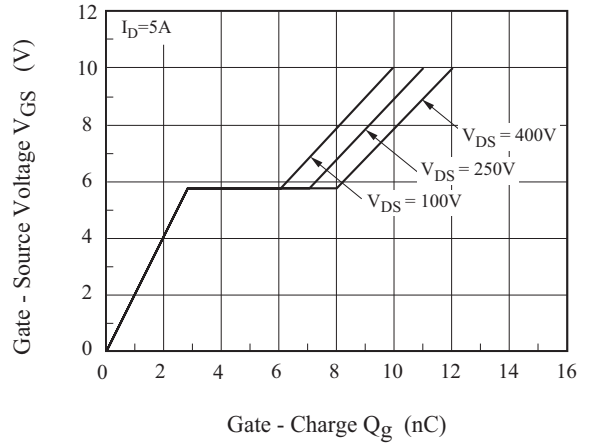


Fig9. Safe Operation Area

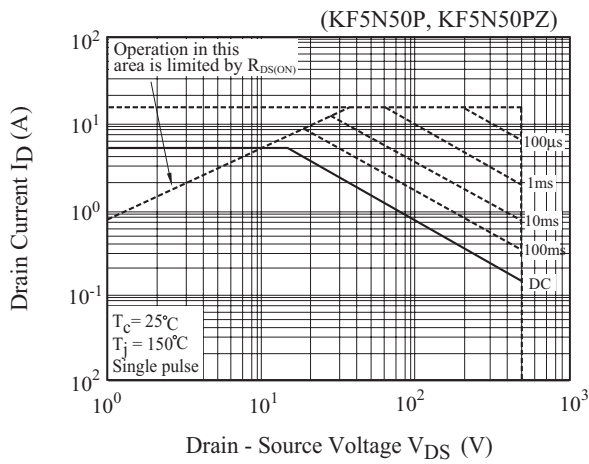


Fig10. Safe Operation Area

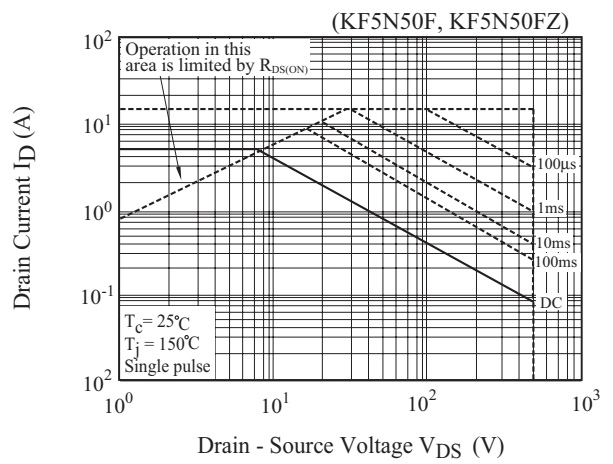
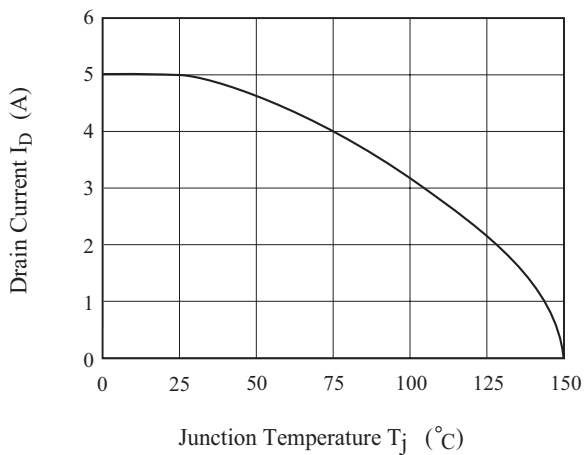


Fig11. I_D - T_j



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Fig12. Transient Thermal Response Curve

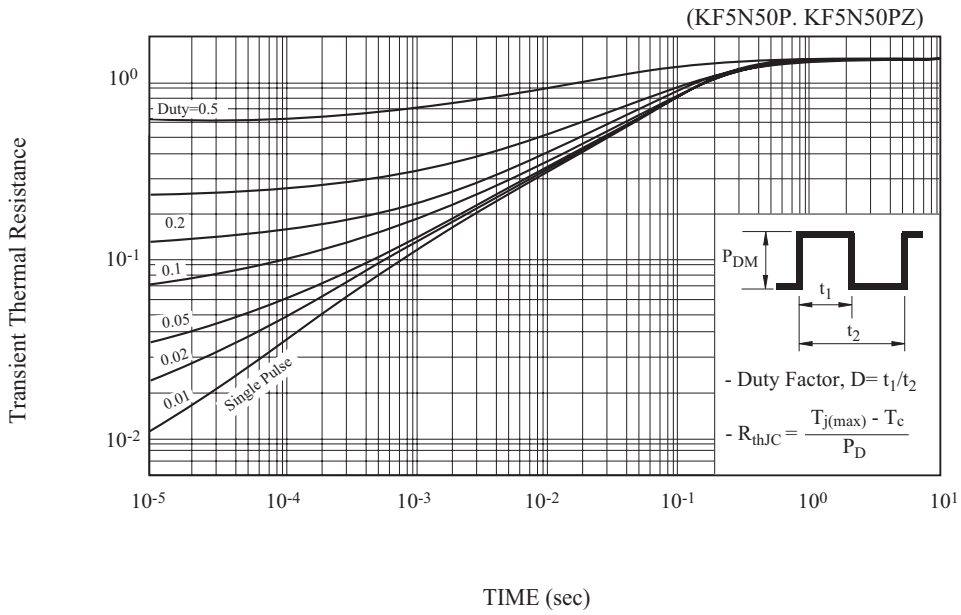
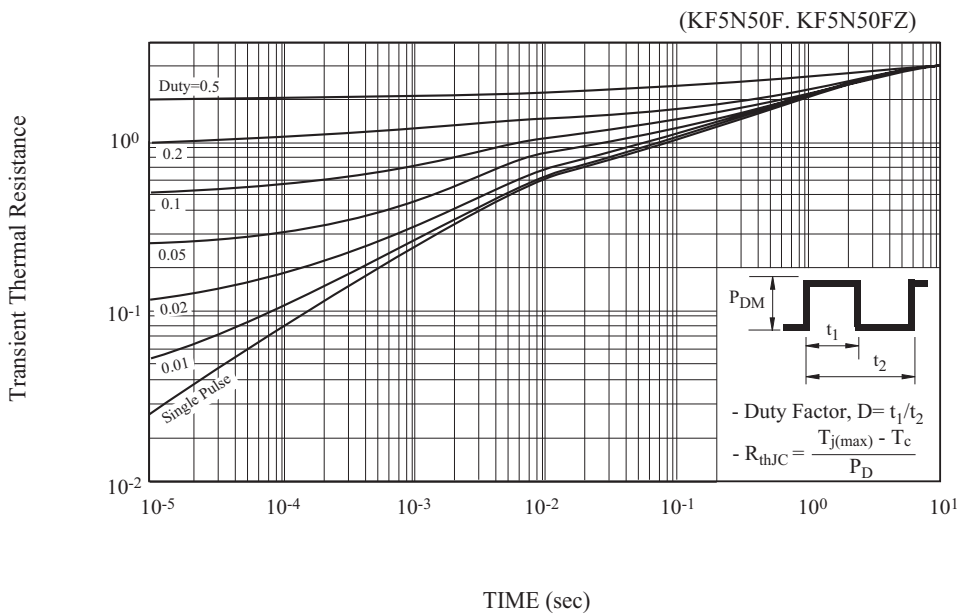


Fig13. Transient Thermal Response Curve



KF5N50P/F/PZ/FZ

Fig14. Gate Charge

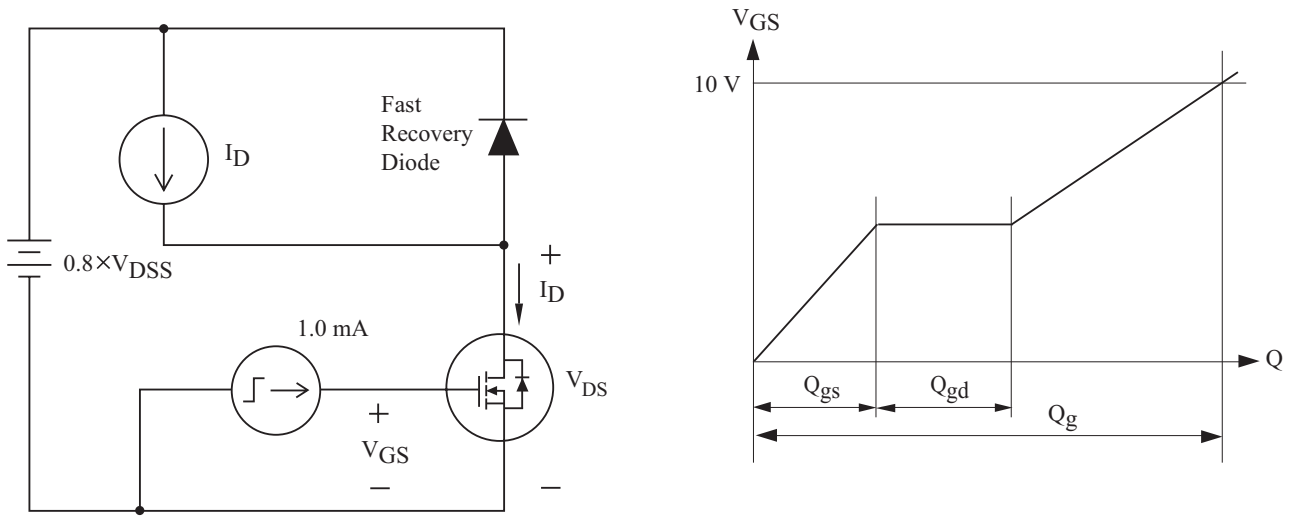


Fig15. Single Pulsed Avalanche Energy

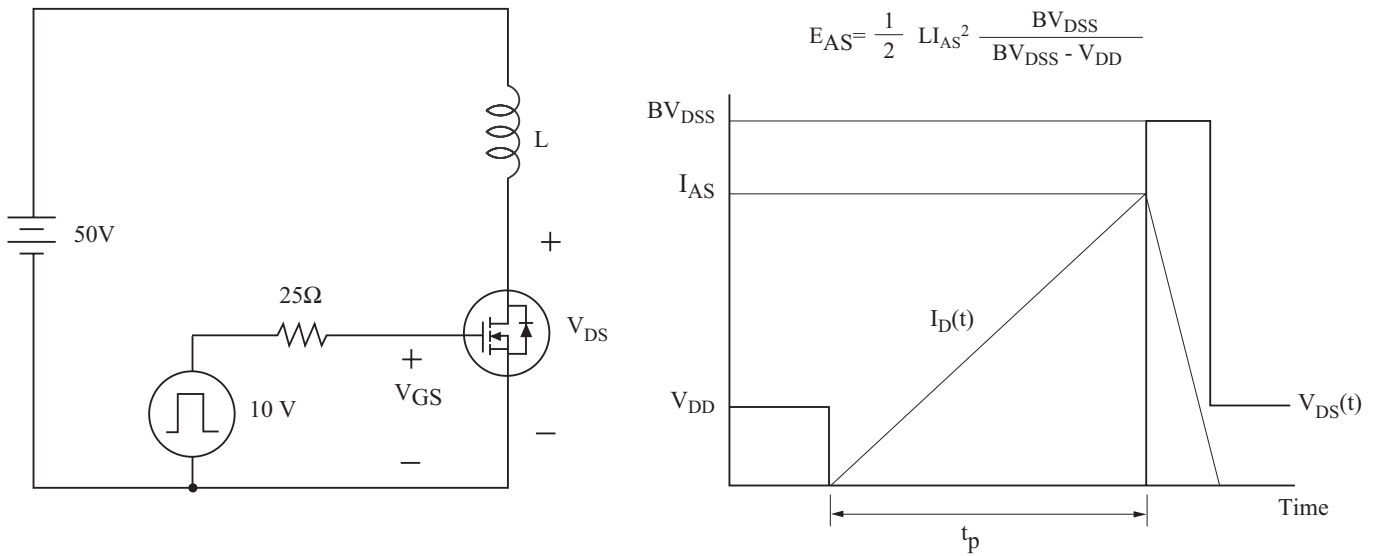


Fig16. Resistive Load Switching

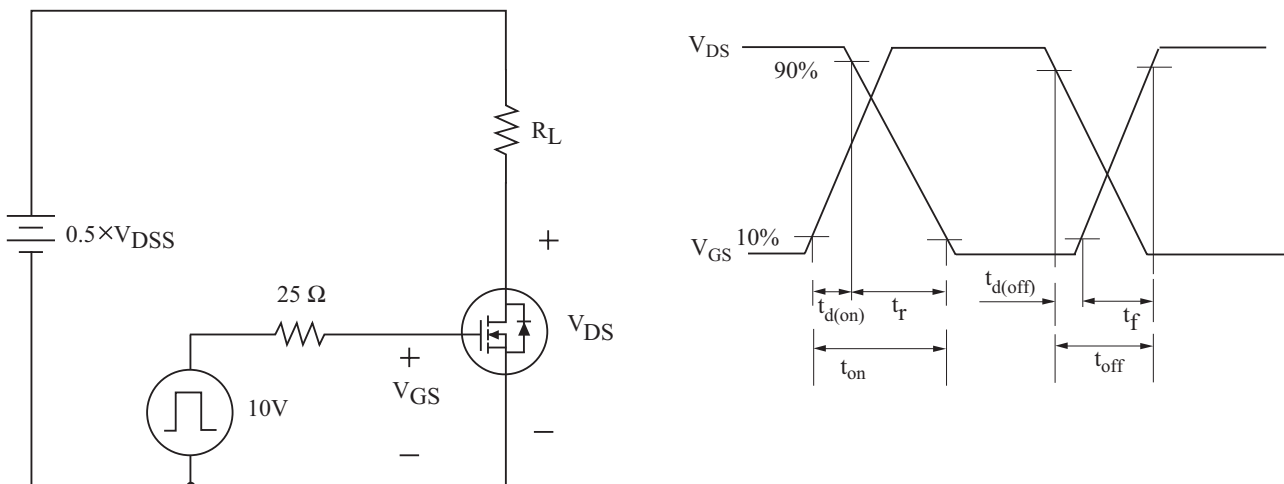


Fig17. Source - Drain Diode Reverse Recovery and dv/dt

